



SEMITRANS® 6

IGBT Modules

SKM25GAH125D

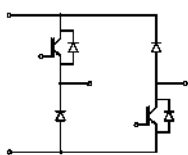
Target Data

Features

- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability, self limiting to $6 \times I_{Cnom}$
- Fast & soft inverse CAL diodes
- Large clearance (10 mm) and creepage distances (20 mm)
- Isolated copper baseplate using DBC Technology (Direct Copper Bonding)
- UL recognized, file no. E63532

Typical Applications*

- DC/DC – converter
- Brake chopper
- Switched reluctance motor
- DC – motor



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Absolute Maximum Ratings

Symbol	Conditions	Values	Unit
IGBT			
V_{CES}	$T_j = 25\text{ °C}$	1200	V
I_C	$T_j = 150\text{ °C}$	$T_c = 25\text{ °C}$	39
		$T_c = 80\text{ °C}$	27
I_{Cnom}		25	A
I_{CRM}	$I_{CRM} = 2 \times I_{Cnom}$	50	A
V_{GES}		-20 ... 20	V
t_{psc}	$V_{CC} = 600\text{ V}$ $V_{GE} \leq 15\text{ V}$ $V_{CES} \leq 1200\text{ V}$	$T_j = 125\text{ °C}$	10
T_j		-55 ... 150	°C
Inverse diode			
I_F	$T_j = 150\text{ °C}$	$T_c = 25\text{ °C}$	47
		$T_c = 80\text{ °C}$	32
I_{Fnom}		40	A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$	80	A
I_{FSM}	$t_p = 10\text{ ms, sin } 180^\circ, T_j = 25\text{ °C}$	410	A
T_j		-40 ... 150	°C
Freewheeling diode			
I_F	$T_j = 150\text{ °C}$	$T_c = 25\text{ °C}$	47
		$T_c = 80\text{ °C}$	32
I_{Fnom}		40	A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$	80	A
I_{FSM}	$t_p = 10\text{ ms, sin } 180^\circ, T_j = 25\text{ °C}$	410	A
T_j		-40 ... 150	°C
Module			
$I_{t(RMS)}$	$T_{terminal} = 80\text{ °C}$	100	A
T_{stg}		-40 ... 125	°C
V_{isol}	AC sinus 50 Hz, $t = 1\text{ min}$	4000	V

Characteristics

Symbol	Conditions	min.	typ.	max.	Unit
IGBT					
$V_{CE(sat)}$	$I_C = 25\text{ A}$ $V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25\text{ °C}$	3.20	3.70	V
		$T_j = 125\text{ °C}$	3.60	4.20	V
V_{CE0}	chipelevel	$T_j = 25\text{ °C}$	1.5	1.75	V
		$T_j = 125\text{ °C}$	1.7	1.95	V
r_{CE}	$V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25\text{ °C}$	68.00	78.00	mΩ
		$T_j = 125\text{ °C}$	76.00	90.00	mΩ
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 1\text{ mA}$	4.5	5.5	6.5	V
I_{CES}	$V_{GE} = 0\text{ V}$ $V_{CE} = 1200\text{ V}$	$T_j = 25\text{ °C}$	0.1	0.3	mA
					mA
C_{ies}	$V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	1.65		nF
C_{oes}	$V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	0.25		nF
C_{res}	$V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	0.11		nF
Q_G	$V_{GE} = -8\text{ V...} + 20\text{ V}$		221		nC
R_{Gint}	$T_j = 25\text{ °C}$		0.00		Ω



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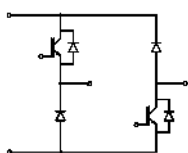
Features

- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability, self limiting to $6 \times I_{cnom}$
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Typical Applications*

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Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
t _{d(on)}	V _{CC} = 600 V	T _j = 125 °C		25		ns
t _r	I _C = 25 A	T _j = 125 °C		19		ns
E _{on}	V _{GE} = ±15 V	T _j = 125 °C		3.9		mJ
t _{d(off)}	R _{G on} = 16 Ω	T _j = 125 °C		184		ns
t _f	R _{G off} = 16 Ω	T _j = 125 °C		8		ns
E _{off}		T _j = 125 °C		1.6		mJ
R _{th(j-c)}	per IGBT				0.56	K/W
Inverse diode						
V _F = V _{EC}	I _F = 40 A	T _j = 25 °C		2.13	2.65	V
	V _{GE} = 0 V chiplevel	T _j = 125 °C		1.94	2.46	V
V _{F0}	chiplevel	T _j = 25 °C		1.1	1.45	V
		T _j = 125 °C		0.85	1.2	V
r _F	chiplevel	T _j = 25 °C		25.7	30.0	mΩ
		T _j = 125 °C		27.1	31.4	mΩ
I _{RRM}	I _F = 25 A	T _j = 125 °C				A
Q _{rr}	V _{GE} = ±15 V V _{CC} = 600 V	T _j = 125 °C				μC
E _{rr}		T _j = 125 °C				mJ
R _{th(j-c)}	per diode				1	K/W
Freewheeling diode						
V _F = V _{EC}	I _F = 40 A	T _j = 25 °C		2.00	2.5	V
	V _{GE} = 0 V chiplevel	T _j = 125 °C		1.8	2.3	V
V _{F0}	chiplevel	T _j = 25 °C		1.1	1.45	V
		T _j = 125 °C		1.18	1.2	V
r _F	chiplevel	T _j = 25 °C		22.5	30.0	mΩ
		T _j = 125 °C		27.1	31.4	mΩ
I _{RRM}	I _F = 25 A	T _j = 125 °C		50		A
Q _{rr}	di/dt _{off} = 2500 A/μs	T _j = 125 °C		4		μC
E _{rr}	V _{GE} = ±15 V V _{CC} = 600 V	T _j = 125 °C		1.1		mJ
R _{th(j-c)}	per Diode				1	K/W
Module						
L _{CE}					60	nH
R _{CC'+EE'}	terminal-chip	T _C = 25 °C				mΩ
		T _C = 125 °C				mΩ
R _{th(c-s)}	per module				0.05	K/W
M _s	to heat sink M6		4		5	Nm
M _t						Nm
						Nm
w					175	g



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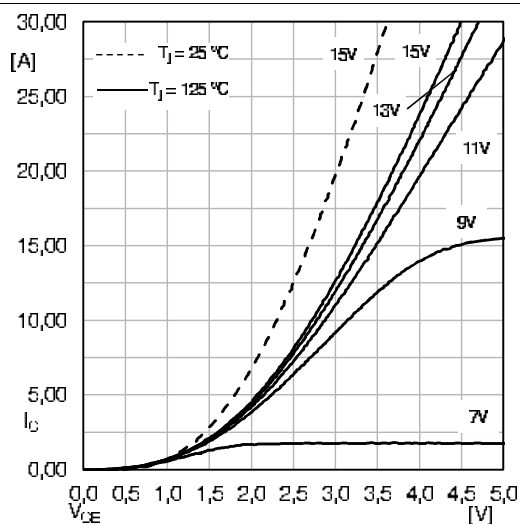


Fig. 1: Typ. output characteristic, inclusive $R_{CC} + EE'$

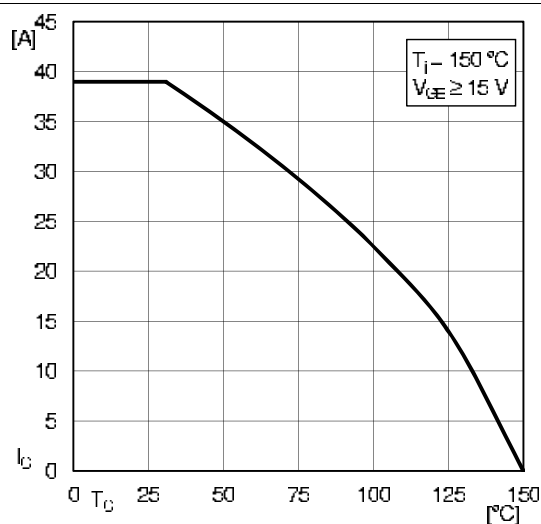


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

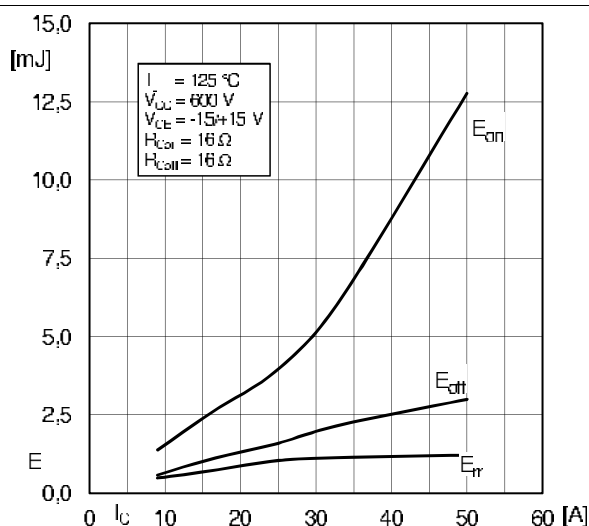


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

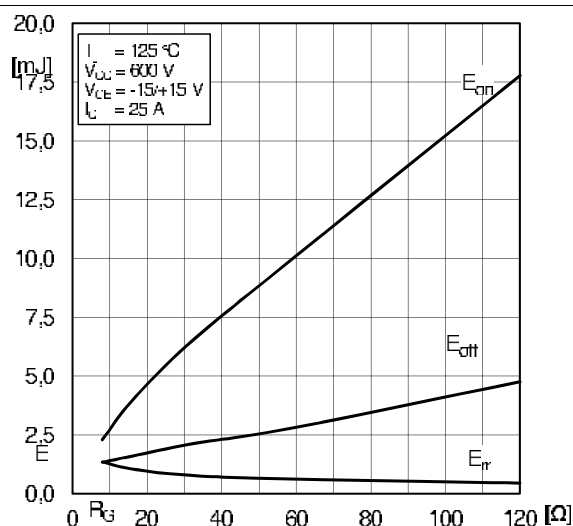


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

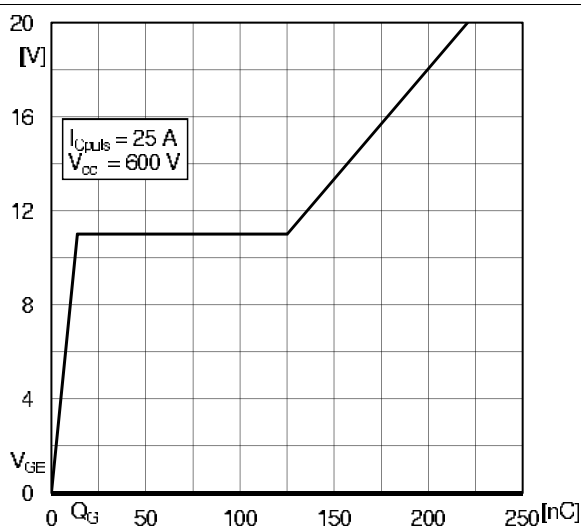


Fig. 6: Typ. gate charge characteristic

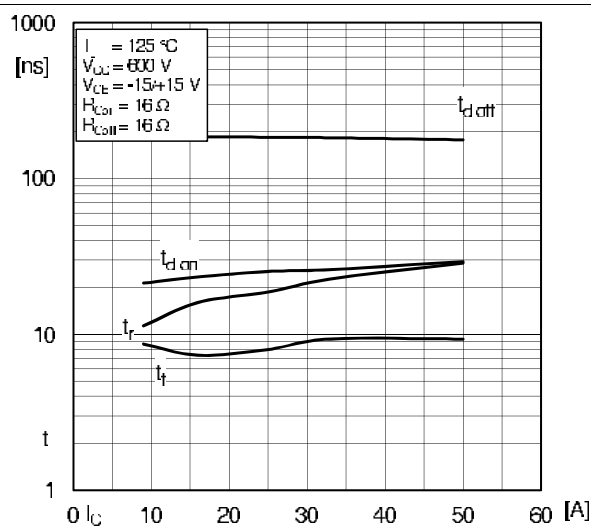


Fig. 7: Typ. switching times vs. I_C

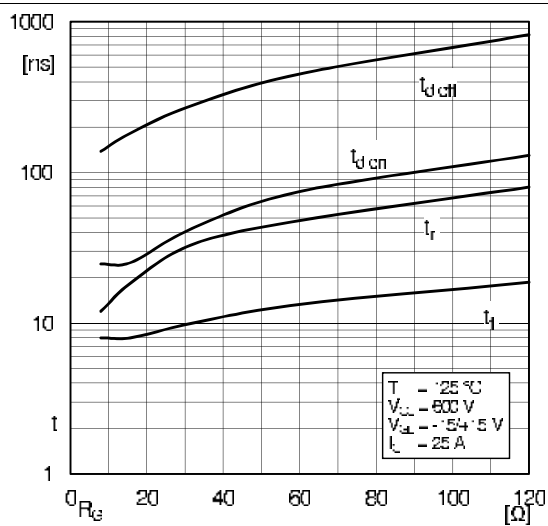


Fig. 8: Typ. switching times vs. gate resistor R_G

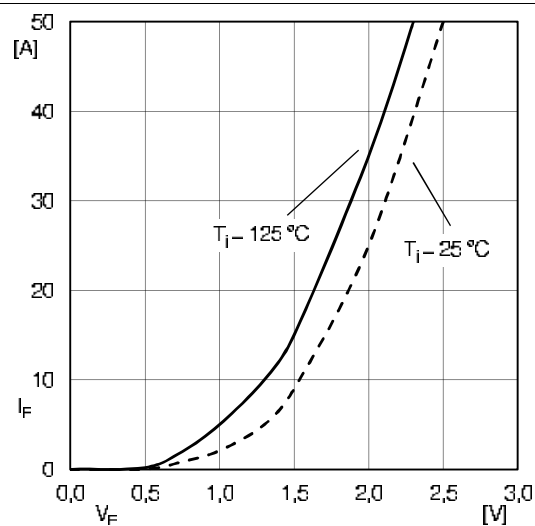
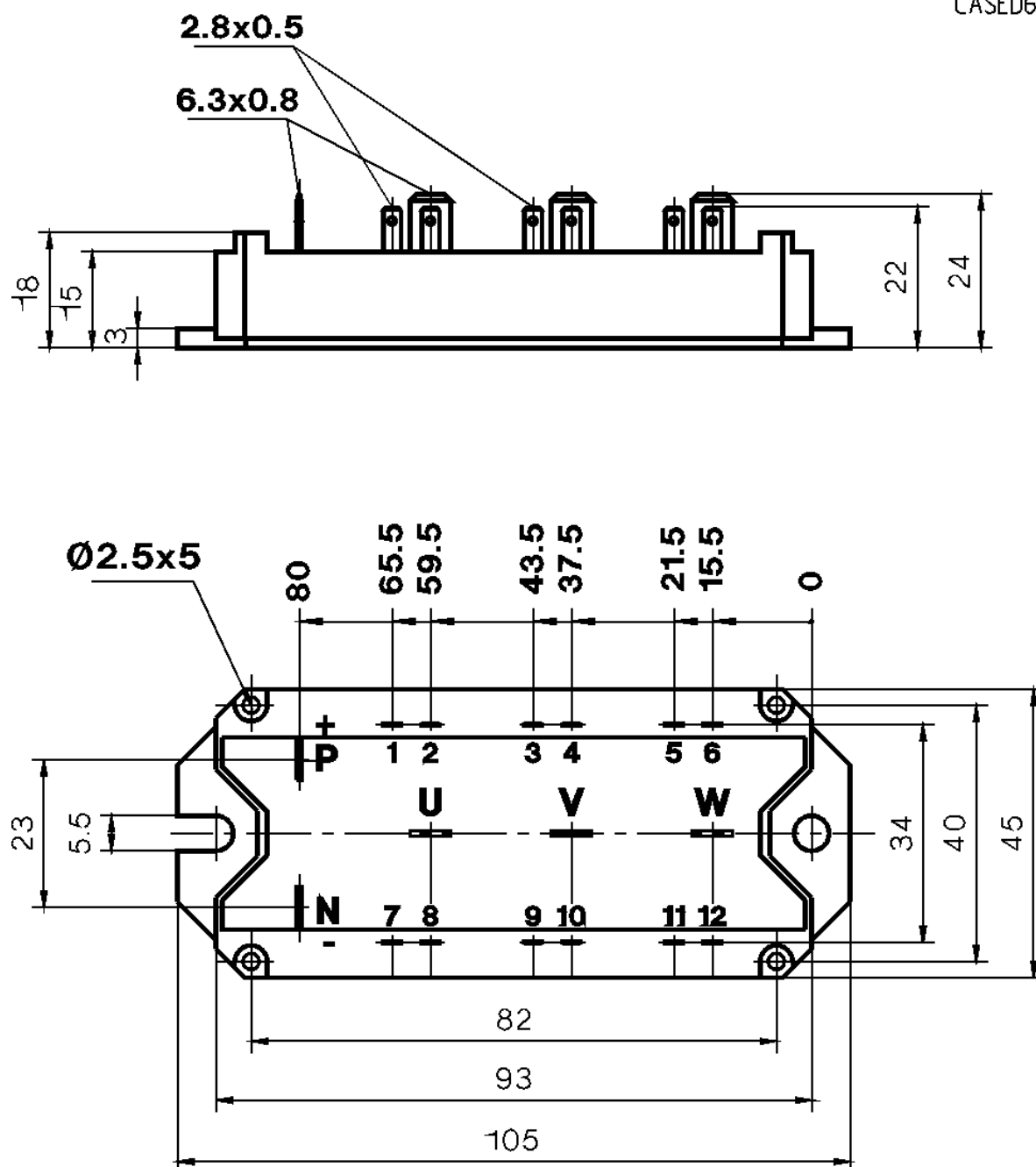
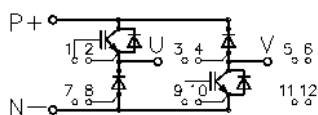


Fig. 10: Typ. CAL diode forward charact., incl. $R_{CC'+EE'}$

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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.